2SA1566

Silicon PNP Epitaxial

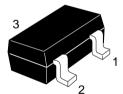
HITACHI

Application

Low frequency amplifier

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector



2SA1566

Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V _{CEO}	-120	V
Emitter to base voltage	V_{EBO}	– 5	V
Collector current	I _c	-100	mA
Collector power dissipation	P _c	150	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

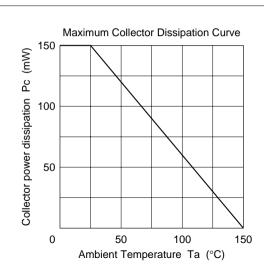
Electrical Characteristics (Ta = 25°C)

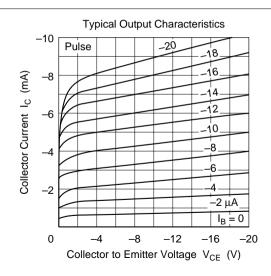
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	_	_	V	$I_{c} = -10 \ \mu A, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 5	_	_	V	$I_{E} = -10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	-0.1	μΑ	$V_{CB} = -70 \text{ V}, I_{E} = 0$
Emitter cutoff current	I_{EBO}	_	_	-0.1	μΑ	$V_{EB} = -2 \text{ V}, I_{C} = 0$
DC current transfer ratio	h _{FE} *1	250	_	800		$V_{CE} = -12 \text{ V}, I_{C} = -2 \text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	_	-0.15	V	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}^{*2}$
Base to emitter voltage	V _{BE(sat)}	_	_	-1.0	V	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}^{*2}$

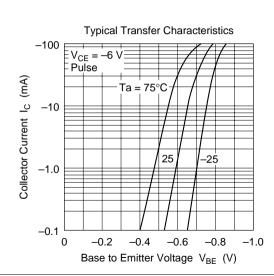
Notes: 1. The 2SA1566 is grouped by h_{FE} as follows.

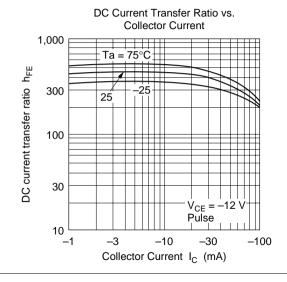
2. Pulse test

Grade	D	E	
Mark	JID	JIE	
h _{FE}	250 to 500	400 to 800	

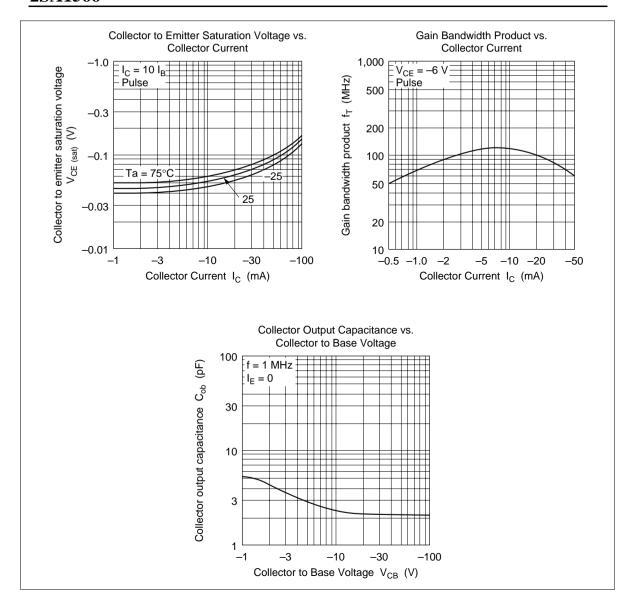




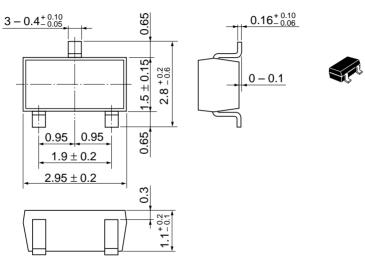




2SA1566



Unit: mm



Hitachi Code	MPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.011 g

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